PCN Number:	20230830001.2A	**PCN Date:**	February 06, 2024
Title:	Qualification of additional Fab Site (RFAB), Die Revision, CDAT as wafer probe site, Assembly BOM options and device marking update for select devices		
Customer Contact:	Change Management team	**Dept:**	Quality Services
Proposed 1st Ship Date:	Feb 26, 2024	**Sample Requests accepted until:**	Sept 30, 2023*

***Sample requests received after Sept 30, 2023 will not be supported.**

Change Type:

☐	Assembly Site	☒	Design	☐	Wafer Bump Material
☒	Assembly Process	☐	Data Sheet	☐	Wafer Bump Process
☒	Assembly Materials	☐	Part number change	☒	Wafer Fab Site
☐	Mechanical Specification	☒	Test Site	☒	Wafer Fab Material
☒	Packing/Shipping/Labeling	☐	Test Process	☐	Wafer Fab Process

PCN Details

Description of Change:

Revision A is to announce the addition of a probe site change & selecting the design check box as a change type which was not included on the original PCN notification.

Texas Instruments is pleased to announce the qualification of RFAB as an additional wafer fab site, die revision, additional assembly BOM options and device marking for the devices listed in the "Product Affected" section.

Current Fab Site			Additional Fab Site		
Current Fab Site	**Process**	**Wafer Diameter**	**Additional Fab Site**	**Process**	**Wafer Diameter**
MIHO	LBC8	200 mm	RFAB	LBC8	300 mm

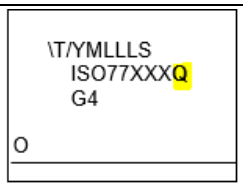
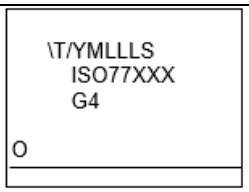
The die was also changed as a result of the process change.

	Current	New
Probe Site (EWS)	None	CDAT (CD-PR)

Assembly BOM options introduced for these devices:

	Current	Proposed
Bond wire diameter composition, diameter	Au, 0.96 mil	0.8 mil Cu

Package marking update:

	Current	Proposed
		
Device marking	With Q	Without Q

Reason for Change:

Continuity of supply.

1) To align with world technology trends and use wiring with enhanced mechanical and electrical properties
2) Maximize flexibility within our Assembly/Test production sites.
3) Cu is easier to obtain and stock

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
☒ No Change	☒ No Change	☒ No Change	☒ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
MIHO8	MH8	JPN	Ibaraki
RFAB	**RFB**	**USA**	**Richardson**

Die Rev:

Current	**New**
Die Rev [2P]	**Die Rev [2P]**
A	**A**

Sample product shipping label (not actual product label)

Product Affected:

ISO7730FQDWRQ1	ISO7731QDWRQ1	ISO7741FQDWRQ1	ISO7742QDWRQ1
ISO7730QDWRQ1	ISO7740FQDWRQ1	ISO7741QDWRQ1	
ISO7731FQDWRQ1	ISO7740QDWRQ1	ISO7742FQDWRQ1	

Qualification Data

Automotive New Product Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)

Approve Date 15-August-2023

Product Attributes

Attributes	Qual Device: ISO7742QDWRQ1	Qual Device: ISO7740QDWRQ1	QBS Reference: UCC23513QDWYQ1	QBS Reference: ISO6763QDWRQ1	QBS Reference: ISO7741QDWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Power Management	Interface	Interface
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB
Assembly Site	MLA	MLA	TAI	MLA	MLA
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	DW	DW	DWY	DW	DW
Pin Count	16	16	6	16	16

QBS: Qual By Similarity
Qual Device ISO7742QDWRQ1 is qualified at MSL2 260C
Qual Device ISO7740QDWRQ1 is qualified at MSL2 260C
Qual Device ISO7730QDWRQ1 is qualified at MSL2 260C
Qual Device ISO7731QDWRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7742QDWRQ1	Qual Device: ISO7740QDWRQ1	QBS Reference: UCC23513QDWYQ1	QBS Reference: ISO6763QDWRQ1	QBS Reference: ISO7741QDWRQ1
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	-	No Fails	No Fails	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	3/231/0	3/231/0	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	3/231/0	3/231/0	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	3/231/0	3/231/0	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	3/135/0	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	3/135/0	-	-
Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	-	-	3/231/0	-	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-	-
Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	3/90/0	3/90/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	3/90/0	3/90/0	1/30/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	-

PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	-	3/30/0	-	1/10/0
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	1/3/0	-	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	-	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0	1/6/0	-	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	1/30/0	3/90/0	3/90/0	1/30/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

For questions regarding this notice, e-mails can be sent to Change Management team or your local Field Sales Representative.

Qualification Data

Automotive New Product Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)

Approve Date 29-June-2023

Product Attributes

Attributes	Qual Device: ISO7741QDWRQ1	QBS Reference: UCC23513QDWYQ1	QBS Reference: ISO6763QDWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Power Management	Interface
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB
Assembly Site	MLA	TAI	MLA
Package Group	SOIC	SOIC	SOIC
Package Designator	DW	DWY	DW
Pin Count	16	6	16

QBS: Qual By Similarity
Qual Device ISO7741QDWRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7741QDWRQ1	QBS Reference: UCC23513QDWYQ1	QBS Reference: ISO6763QDWRQ1
Test Group A - Accelerated Environment Stress Tests										
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	No Fails	No Fails
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	3/135/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	3/135/0	-
Test Group B - Accelerated Lifetime Simulation Tests										
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	-	3/231/0	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-
Test Group C - Package Assembly Integrity Tests										
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0

SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	-
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	-
Test Group D - Die Fabrication Reliability Tests										
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests										
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	3/90/0	3/90/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Automotive New Product Qualification Summary
(As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)
Approve Date 20-June-2023

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1
Test Group A - Accelerated Environment Stress Tests								
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	No Fails
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	-
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	3/9/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-
TC	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-
TC	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	-
TC	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	-
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0
TC	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	3/9/0
TC	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0
TC	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	3/9/0

HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0
Test Group B - Accelerated Lifetime Simulation Tests								
Test Group C - Package Assembly Integrity Tests								
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-
Test Group D - Die Fabrication Reliability Tests								
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements

QBS: Qual By Similarity
Qual Device ISO6763QDWRQ1 is qualified at MSL2 260C
Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
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E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

ZVEI ID reference: SEM-DE-03, SEM-PW-13, SEM-PW-02, SEM-PA-08, SEM-PA-13, SEM-TF-01

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